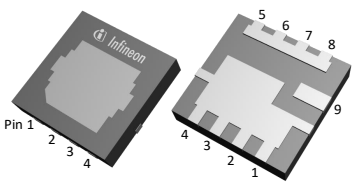
MOSFET

OptiMOS™ 5 Power-Transistor, 100 V

PG-WHTFN-9



Features

- Optimized for high performance SMPS, e.g. syncronous rectification
- N-channel
- 100% avalanche tested
- Superior thermal resistance
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

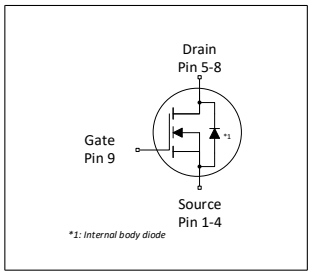


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	6.5	mΩ
I_D	85	A
Q_{oss}	40	nC
Q_G(0V...10V)	34	nC

Type / Ordering Code	Package	Marking	Related Links
IQE065N10NM5CGSC	PG-WHTFN-9	S	-

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - - -	- - - -	85 60 46 13	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=6 V, T_C=100 °C V_{GS}=10V, T_A=25°C,R_{thJA}=60°C/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	340	A	T_A=25 °C
Avalanche energy, single pulse[4]	E_{AS}	-	-	147	mJ	I_D=20 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	100 2.5	W	T_C=25 °C T_A=25 °C, R_{thJA}=60 °C/W[2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.8	1.5	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	0.7	-	°C/W	-
Thermal resistance, junction - ambient, 6 cm² cooling area[2]	R_{thJA}	-	-	60	°C/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	V_{DS}=V_{GS}, I_D=48 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1.0 100	µA	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	5.7 7.2	6.5 11	mΩ	V_{GS}=10 V, I_D=20 A V_{GS}=6 V, I_D=10 A
Gate resistance	R_G	-	0.7	-	Ω	-
Transconductance	g_{fs}	-	55	-	S	$\|V_{DS}\|\geq 2\|I_D\|R_{DS(on)max}$, I_D=20 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1)]	C_{iss}	-	2300	3000	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	340	440	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance[1)]	C_{rss}	-	18	32	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	8.9	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	3.8	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	21.1	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	7.5	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	10.1	-	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 10 V
Gate charge at threshold	$Q_{g(th)}$	-	6.8	-	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 10 V
Gate to drain charge[1)]	Q_{gd}	-	7.4	11.1	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	10.7	-	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 10 V
Gate charge total[1)]	Q_g	-	34	43.0	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.4	-	V	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	29	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 10 V
Output charge[1)]	Q_{oss}	-	40	53	nC	V_{DS}=50 V, V_{GS}=0 V

[1)] Defined by design. Not subject to production test.
[2)] See ″Gate charge waveforms″ for parameter definition

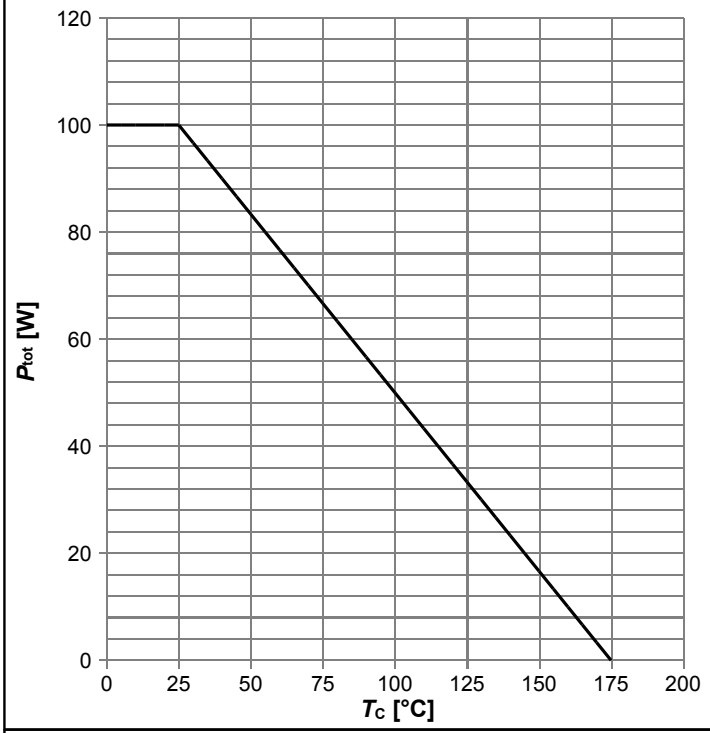
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	74	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	340	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.83	1.1	V	V_{GS}=0 V, I_F=20 A, T_j=25 °C
Reverse recovery time[1)]	t_{rr}	-	36	72	ns	V_R=50 V, I_F=20 A, di_F/dt=100 A/µs
Reverse recovery charge[1)]	Q_{rr}	-	40	80	nC	V_R=50 V, I_F=20 A, di_F/dt=100 A/µs

[1)] Defined by design. Not subject to production test.

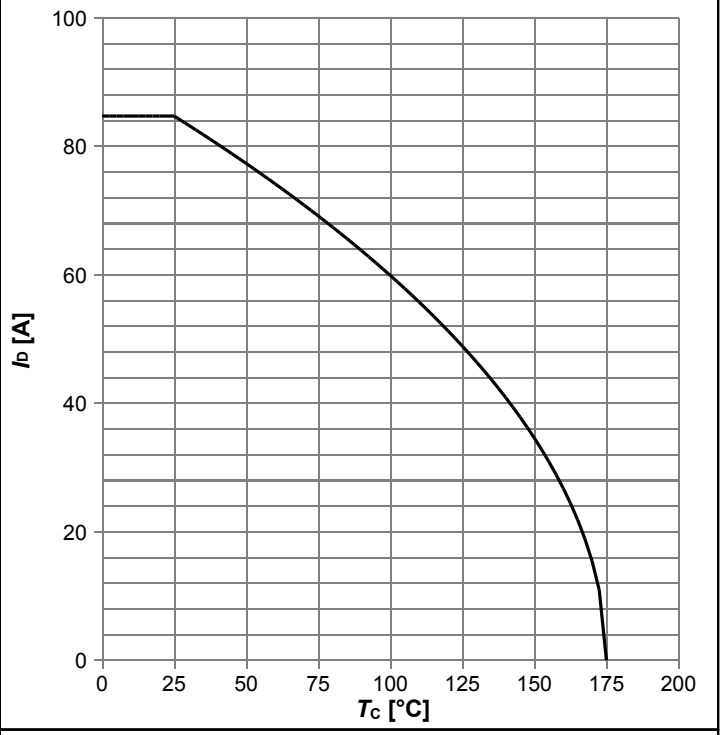
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



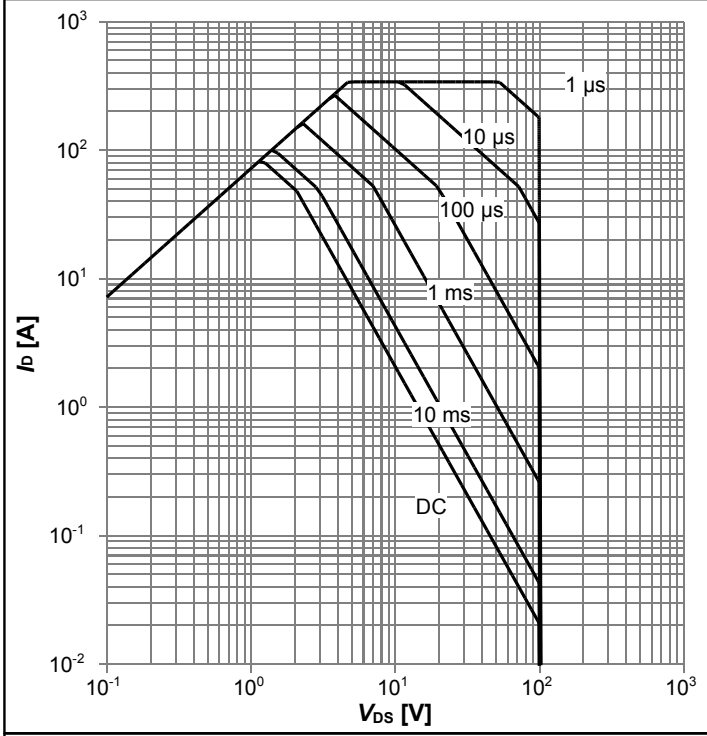
$P_{tot}=f(T_C)$

Diagram 2: Drain current



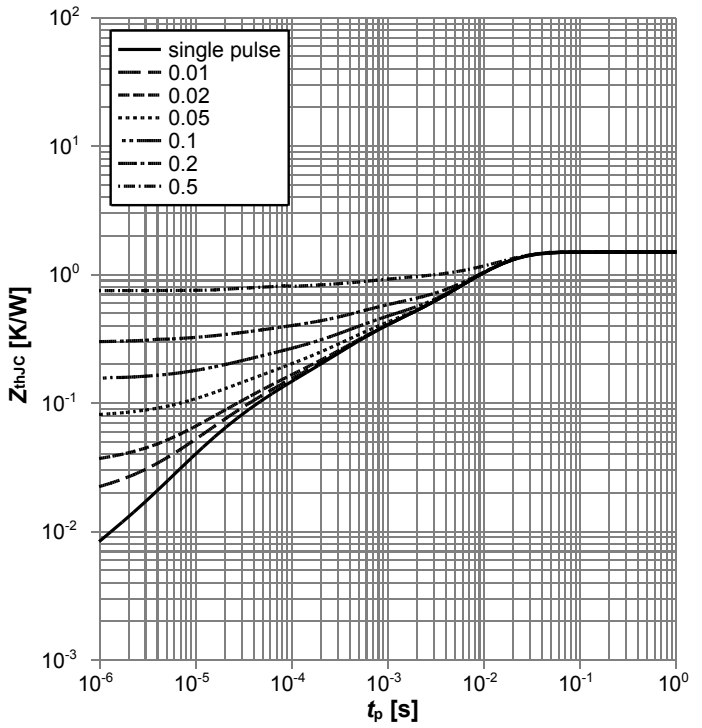
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



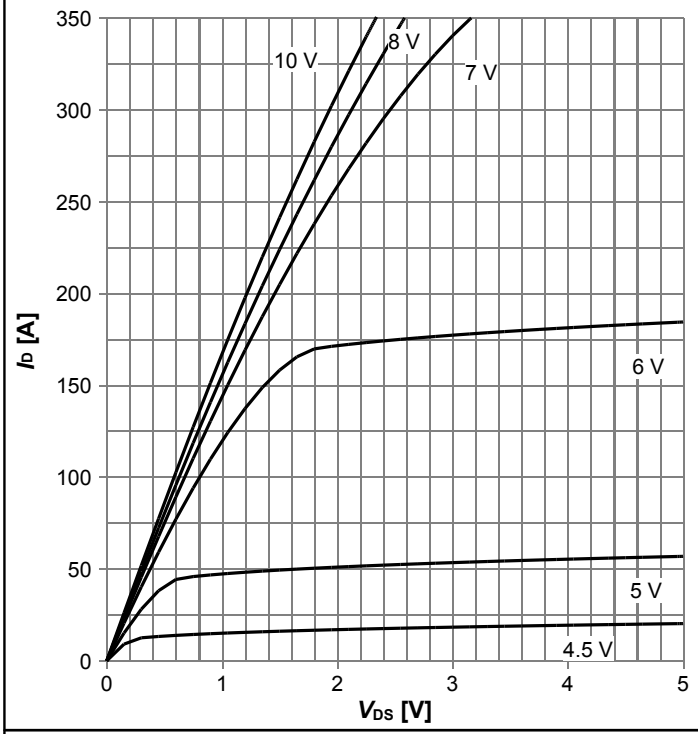
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



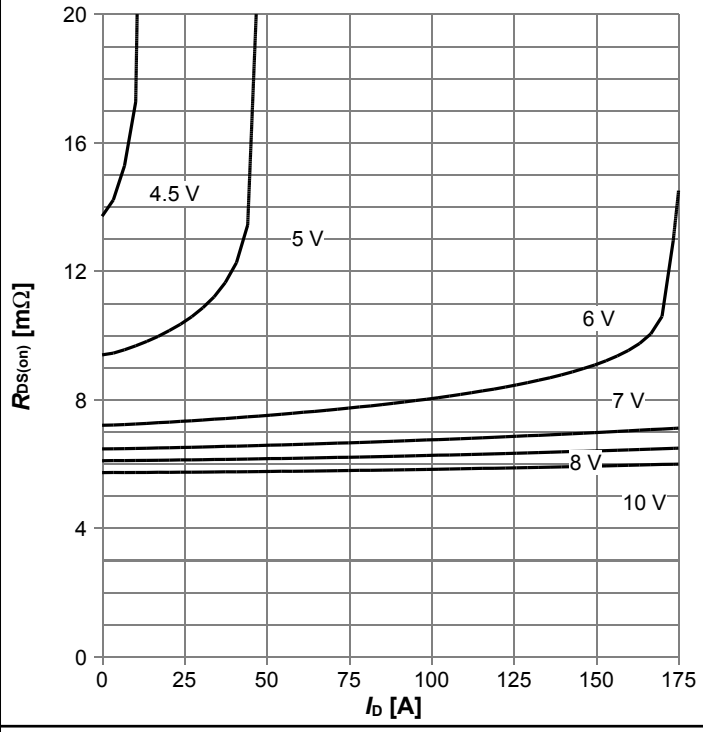
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



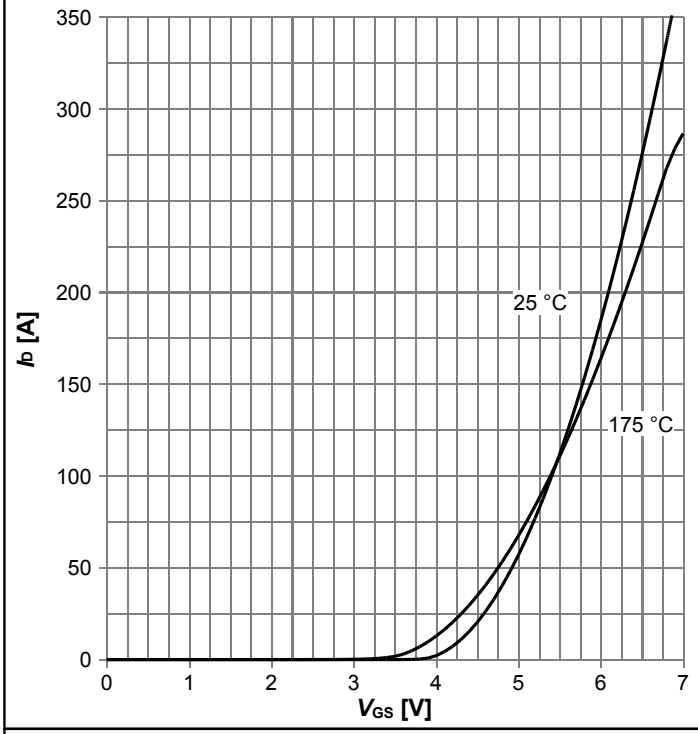
$I_D=f(V_{DS})$, $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



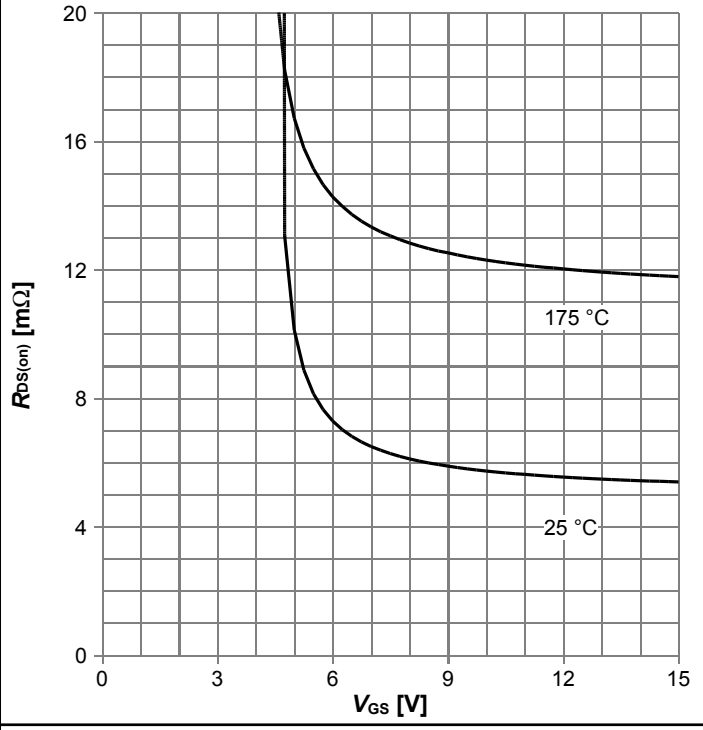
$R_{DS(on)}=f(I_D)$, $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



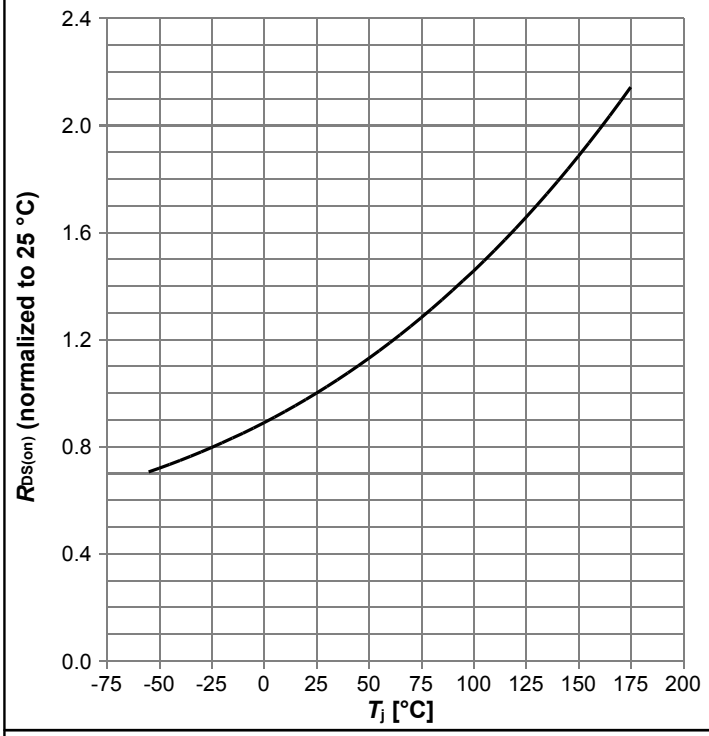
$I_D=f(V_{GS})$, $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



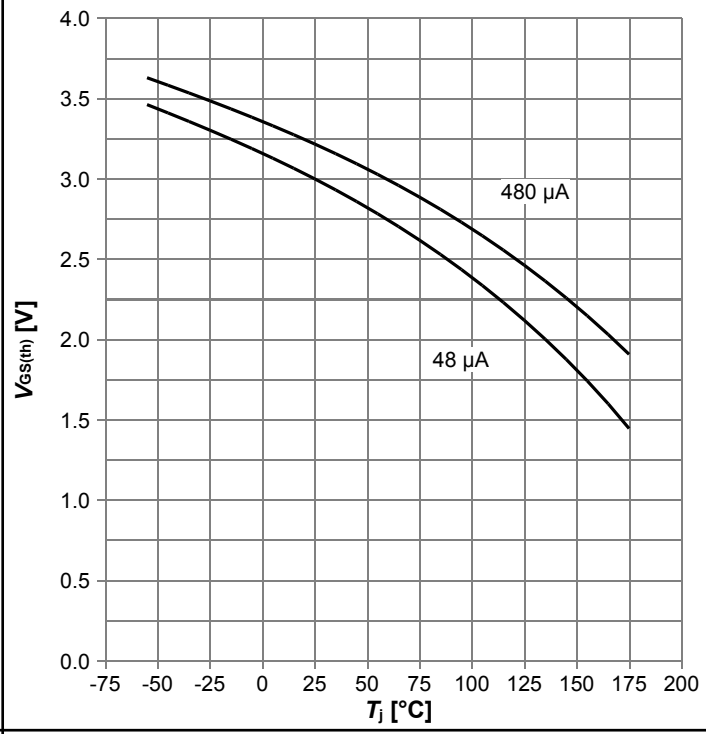
$R_{DS(on)}=f(V_{GS})$, $I_D=20$ A; parameter: T_j

Diagram 9: Normalized drain-source on resistance



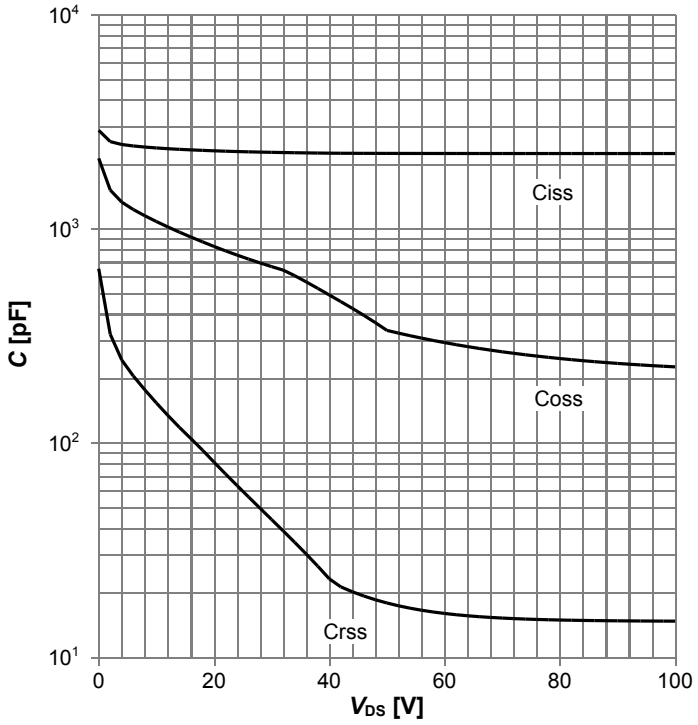
$R_{DS(on)}$=f(T_j), I_D=20 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



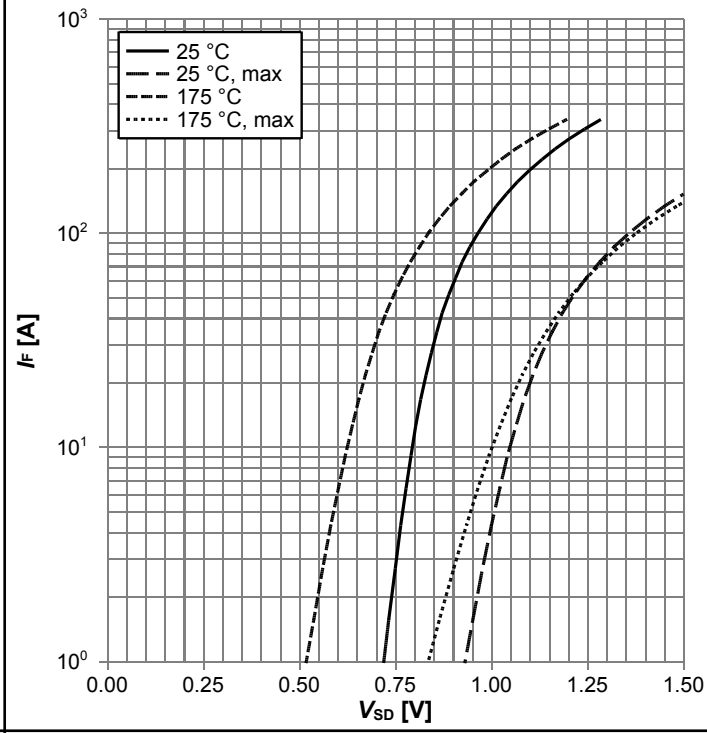
$V_{GS(th)}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



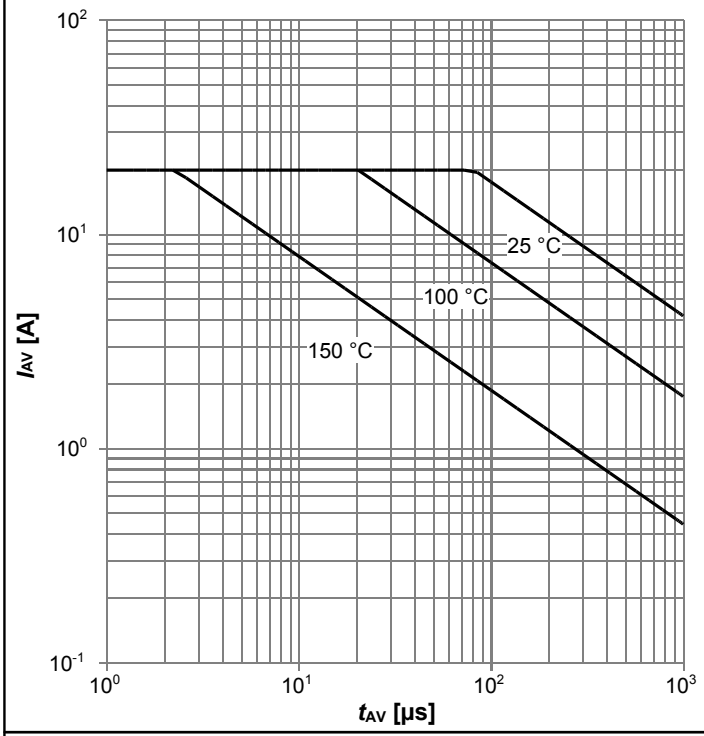
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



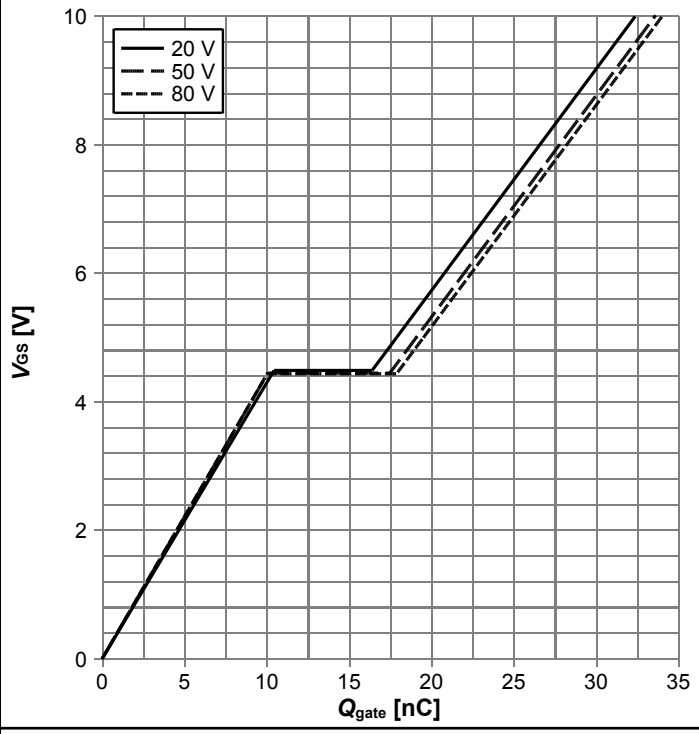
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



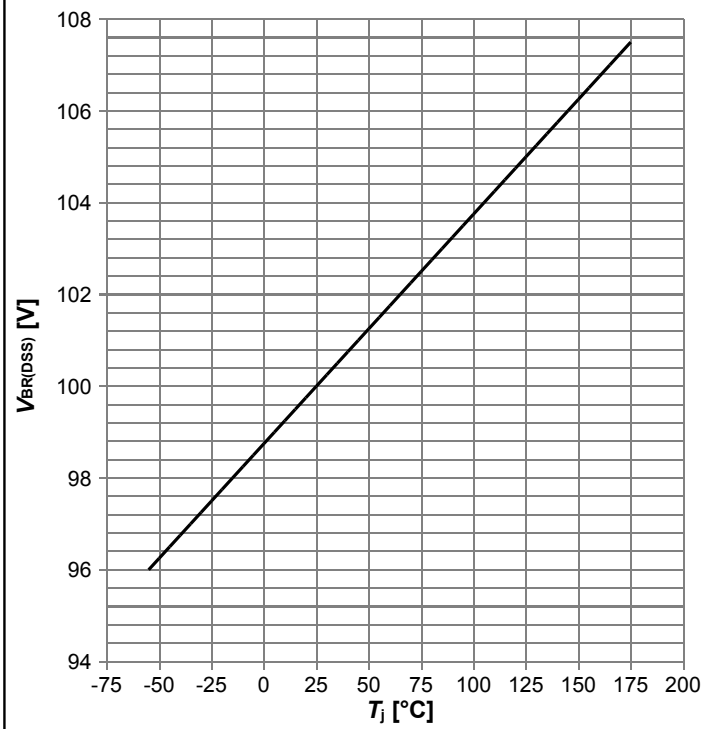
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



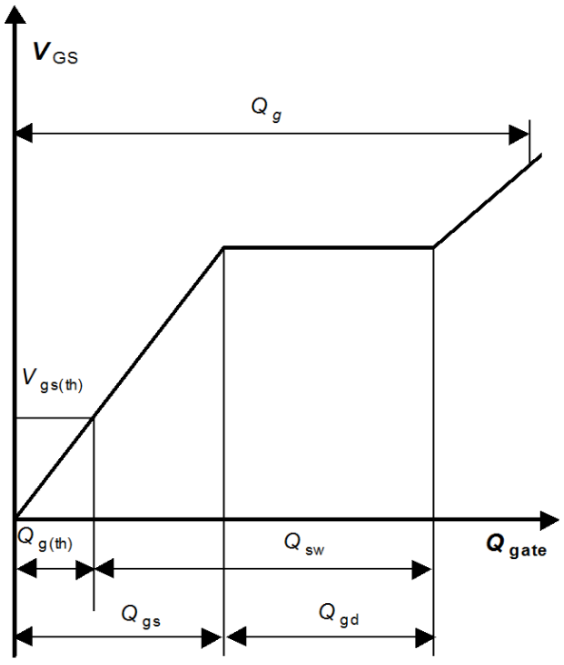
$V_{GS}=f(Q_{gate})$, $I_D=20$ A pulsed, $T_j=25$ °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

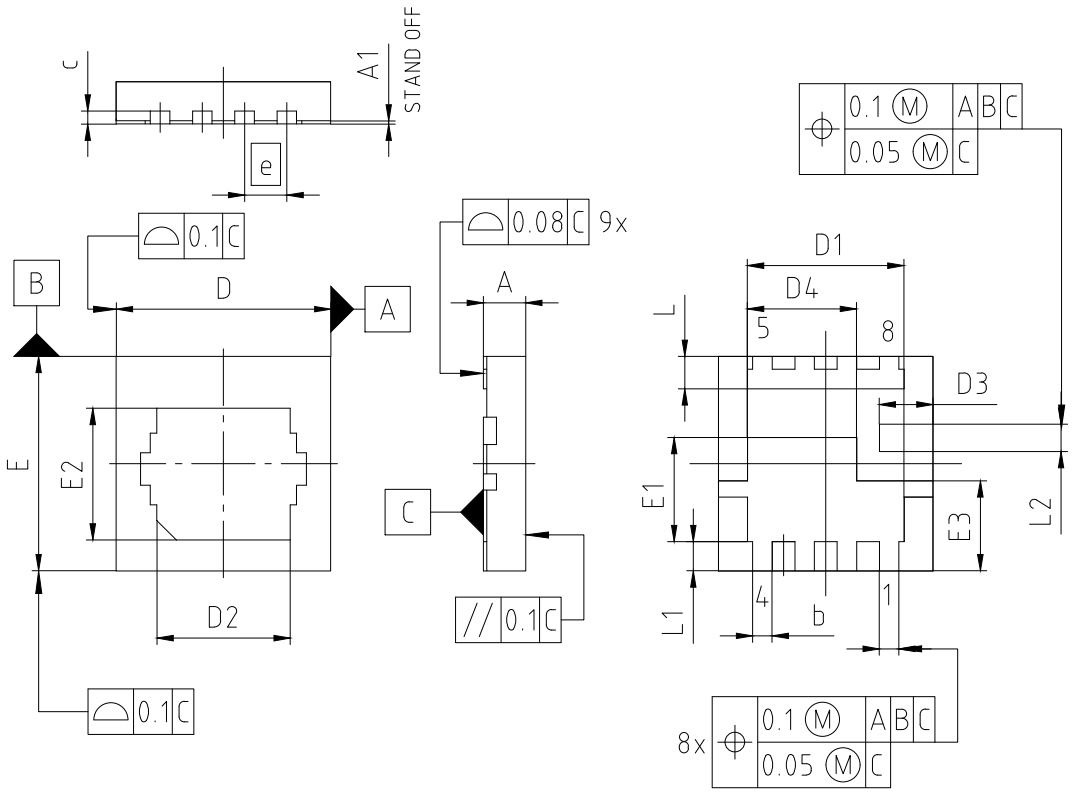


$V_{BR(DSS)}=f(T_j)$; $I_D=1$ mA

Diagram Gate charge waveforms



5 Package Outlines



PACKAGE - GROUP NUMBER:	PG-WHTFN-9-U01	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	---	0.75
A1	0	0.05
b	0.20	0.40
c	0.10	0.30
D	3.20	3.40
D1	2.31	2.51
D2	1.95	2.25
D3	0.73	0.93
D4	1.58	1.78
E	3.20	3.40
E1	1.50	1.70
E2	1.93	2.23
E3	1.285	1.485
e	0.65	
L	0.40	0.60
L1	0.35	0.55
L2	0.32	0.52

Figure 1 Outline PG-WHTFN-9, dimensions in mm

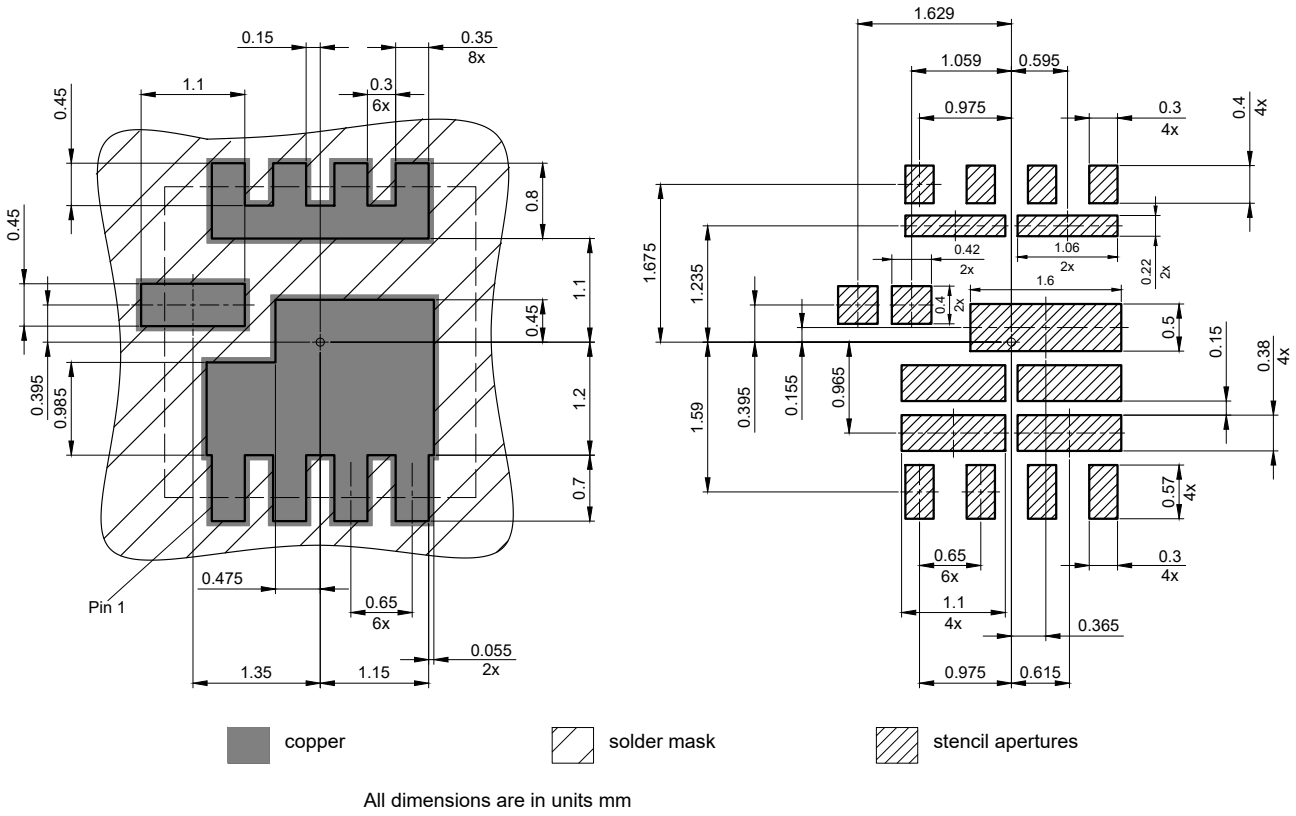


Figure 2 Outline Footprint (PG-WHTFN-9-1), dimensions in mm

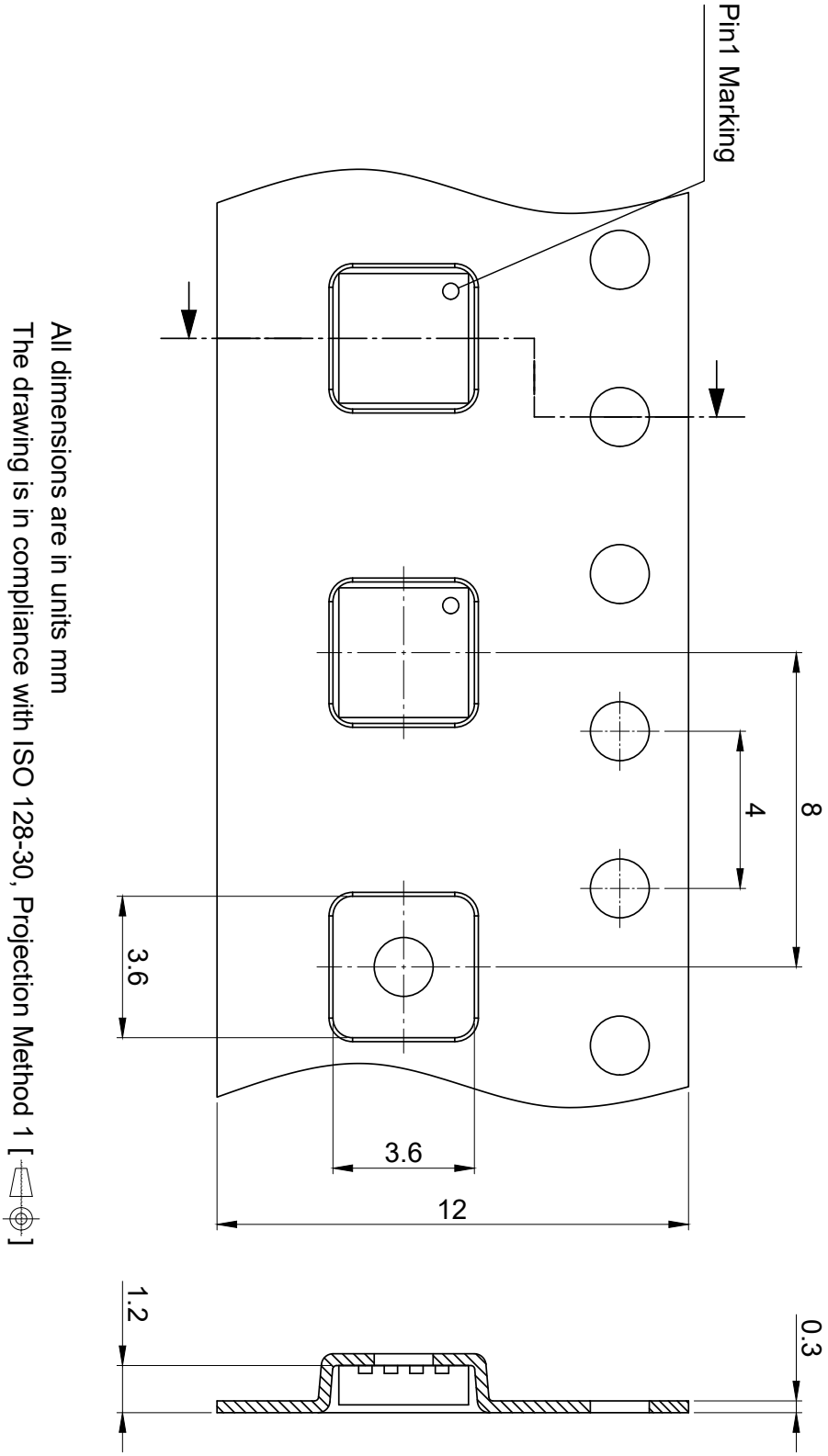


Figure 3 Outline Tape (PG-WHTFN-9-1), dimensions in mm

Revision History

IQE065N10NM5CGSC

Revision: 2022-05-02, Rev. 2.0

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2022-05-02	Release of final version

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